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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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General Purpose Transistor

NPN Silicon

Features

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ic	200	mAdc
Collector Current – Peak (Note 3)	I _{CM}	900	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

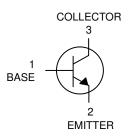
1

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
- 3. Reference SOA curve.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



1AM = Specific Device Code

M = Date Code* ■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]		
MMBT3904LT1G	SOT-23	3000 / Tape &		
SMMBT3904LT1G	(Pb-Free)	Reel		
MMBT3904LT3G	SOT-23	10,000 / Tape &		
SMMBT3904LT3G	(Pb-Free)	Reel		

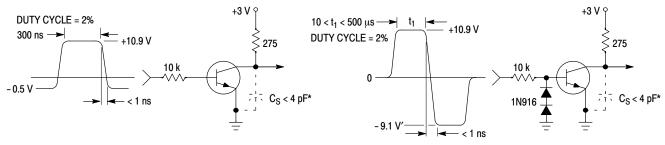
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Chara	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS		1				
Collector - Emitter Breakdown Voltage (Id	V _{(BR)CEO}	40	-	Vdc		
Collector – Base Breakdown Voltage (I _C =	= 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	-	Vdc	
Emitter – Base Breakdown Voltage (I _E =	10 μ Adc, I _C = 0)	V _{(BR)EBO}	6.0	-	Vdc	
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB}	= 3.0 Vdc)	I _{BL}	-	50	nAdc	
Collector Cutoff Current (V _{CE} = 30 Vdc, V	V _{EB} = 3.0 Vdc)	I _{CEX}	-	50	nAdc	
ON CHARACTERISTICS (Note 4)						
	(I _C = 0.1 mAdc, V _{CE} = 1.0 Vdc) (I _C = 1.0 mAdc, V _{CE} = 1.0 Vdc) (I _C = 10 mAdc, V _{CE} = 1.0 Vdc) (I _C = 50 mAdc, V _{CF} = 1.0 Vdc)		40 70 100 60 30	- 300 - -	-	
		V _{CE(sat)}	- -	0.2 0.3	Vdc	
	V _{BE(sat)}	0.65 -	0.85 0.95	Vdc		
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain - Bandwidth Product (I _C =	= 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	-	MHz	
Output Capacitance (V _{CB} = 5.0 Vdc, I _E =	0, f = 1.0 MHz)	C _{obo}	_	4.0	pF	
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0), f = 1.0 MHz)	C _{ibo}	_	8.0	pF	
Input Impedance (V _{CE} = 10 Vdc, I _C = 1.0	mAdc, f = 1.0 kHz)	h _{ie}	1.0	10	kΩ	
Voltage Feedback Ratio (V _{CE} = 10 Vdc,	I _C = 1.0 mAdc, f = 1.0 kHz)	h _{re}	0.5	8.0	X 10 ⁻⁴	
Small-Signal Current Gain (V _{CE} = 10 Vo	h _{fe}	100	400	-		
Output Admittance ($V_{CE} = 10 \text{ Vdc}, I_{C} = 1$	h _{oe}	1.0	40	μmhos		
Noise Figure ($V_{CE} = 5.0 \text{ Vdc}$, $I_{C} = 100 \mu M$	NF	-	5.0	dB		
SWITCHING CHARACTERISTICS						
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc},$	t _d	_	35		
Rise Time	$I_C = 10 \text{ mAdc}, I_{B1} = 1.0 \text{ mAdc})$	t _r	_	35	ns	
Storage Time	(V _{CC} = 3.0 Vdc,	t _s	_	200		
Fall Time	$I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	t _f	_	50	ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{4.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

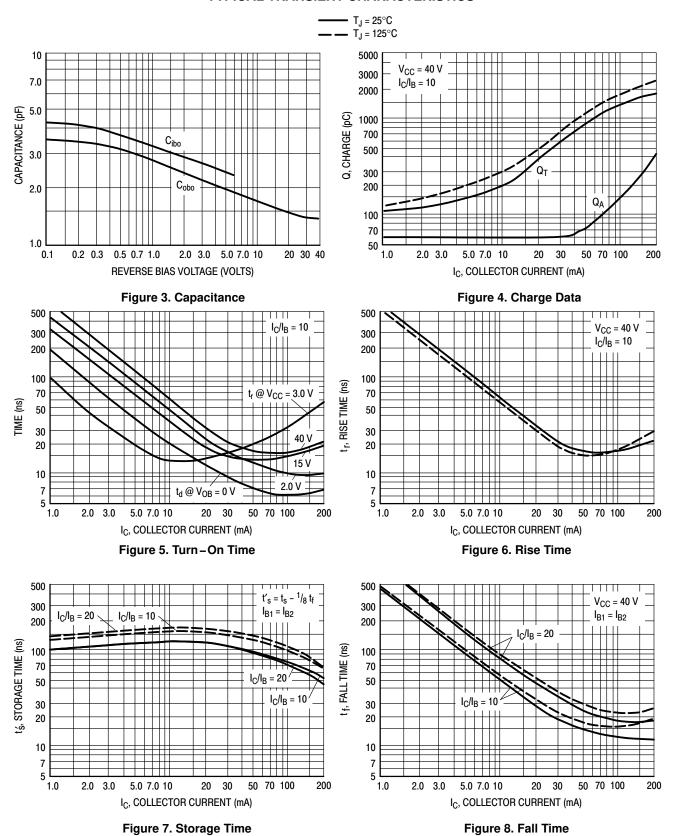


^{*} Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



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TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$

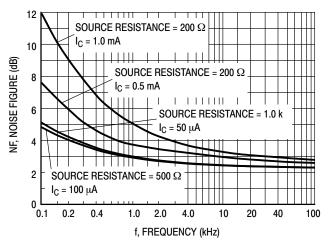
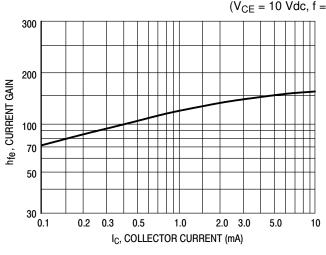


Figure 9.

Figure 10.

h PARAMETERS



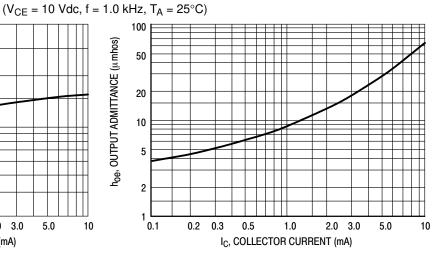


Figure 11. Current Gain

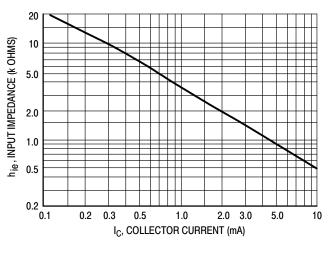


Figure 12. Output Admittance

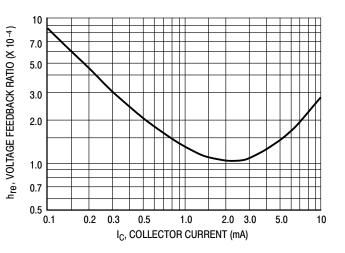


Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

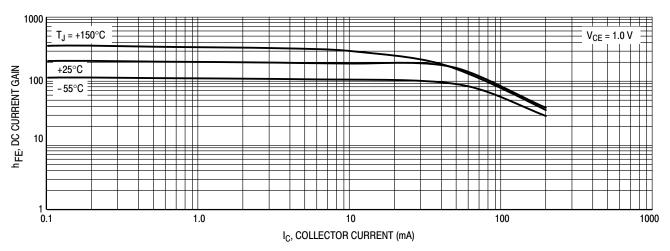


Figure 15. DC Current Gain

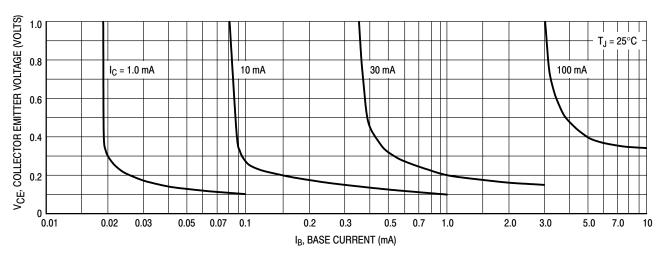


Figure 16. Collector Saturation Region

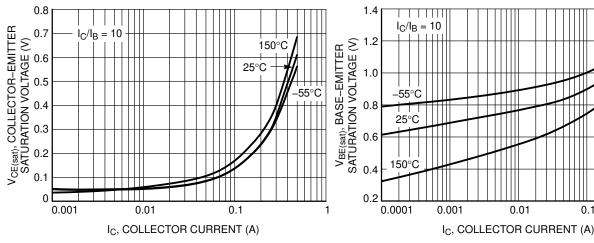


Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

Figure 18. Base Emitter Saturation Voltage vs. Collector Current

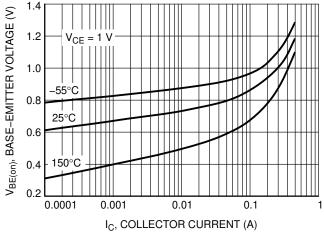


Figure 19. Base Emitter Voltage vs. Collector Current

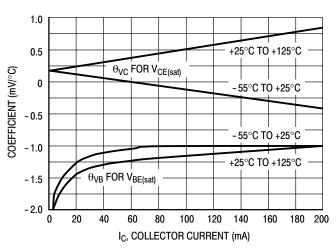


Figure 20. Temperature Coefficients

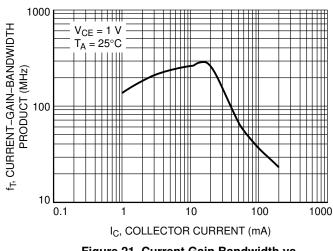


Figure 21. Current Gain Bandwidth vs. Collector Current

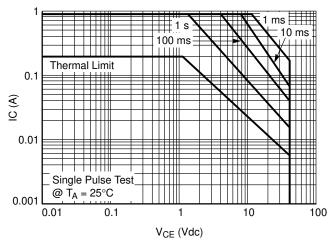
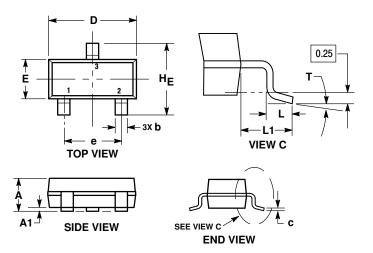


Figure 22. Safe Operating Area

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**



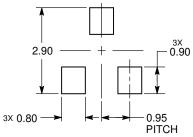
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

STYLE 6:

- PIN 1. BASE
 - EMITTER 2.
 - COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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